
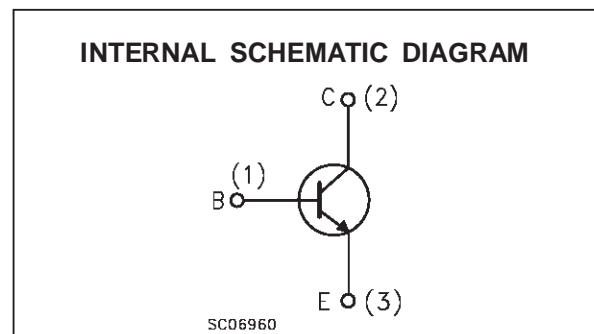
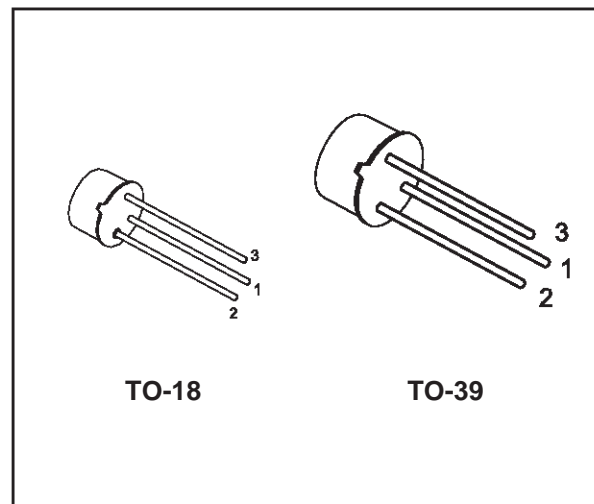


## HIGH SPEED SWITCHES

### DESCRIPTION

The 2N2219A and 2N2222A are silicon planar epitaxial NPN transistors in Jedec TO-39 (for 2N2219A) and in Jedec TO-18 (for 2N2222A) metal case. They are designed for high speed switching application at collector current up to 500mA, and feature useful current gain over a wide range of collector current, low leakage currents and low saturation voltage.

 2N2219A approved to CECC 50002-100,  
2N2222A approved to CECC 50002-101  
available on request.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	75	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	40	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	6	V
$I_C$	Collector Current	0.8	A
$P_{tot}$	Total Dissipation at $T_{amb} \leq 25\text{ }^\circ\text{C}$ for <b>2N2219A</b> for <b>2N2222A</b> at $T_{case} \leq 25\text{ }^\circ\text{C}$ for <b>2N2219A</b> for <b>2N2222A</b>	0.8	W
		0.5	W
		3	W
		1.8	W
$T_{stg}$	Storage Temperature	-65 to 200	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	175	$^\circ\text{C}$